BTA204X series B and C

GENERAL DESCRIPTION

Passivated high commutation triacs in a plastic full pack envelope intended for use in circuits where high static and dynamic dV/dt and high dl/dt can occur. These devices will commutate the full rated rms current at the maximum rated junction temperature without the aid of a snubber.

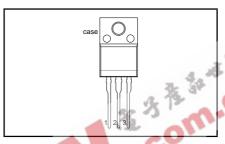
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	MAX.	MAX.	UNIT
	BTA204X- BTA204X-	500B 500C	600B 600C	800B 800C	
V_{DRM}	Repetitive peak	500	600	800	V
I _{T(RMS)} I _{TSM}	off-state voltages RMS on-state current Non-repetitive peak on-state current	4 25	4 25	4 25	A A

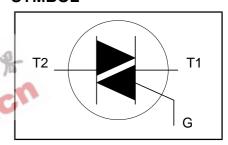
PINNING - SOT186A

PIN	DESCRIPTION			
1	main terminal 1			
2	main terminal 2			
3	gate			
case	isolated			

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.		MAX.		UNIT
V _{DRM}	Repetitive peak off-state voltages		-	-500 500 ¹	-600 600 ¹	-800 800	V
I _{T(RMS)}	RMS on-state current	full sine wave;	-		4		Α
I _{TSM}	Non-repetitive peak on-state current	$T_{hs} \le 92$ °C full sine wave; $T_j = 25$ °C prior to surge t = 20 ms t = 16.7 ms	-		25 27		A A
l²t dl _⊤ /dt	I ² t for fusing Repetitive rate of rise of on-state current after triggering	t = 10.7 ms t = 10 ms I _{TM} = 6 A; I _G = 0.2 A; dI _G /dt = 0.2 A/µs	-	3.1 100		A ² s A/μs	
I _{GM} V _{GM} P _{GM} P _{G(AV)}	Peak gate current Peak gate voltage Peak gate power Average gate power	over any 20 ms period			2 5 5 0.5		A V W W
$T_{stg} T_{j}$	Storage temperature Operating junction temperature	Poriod	-40 -		150 125		္ငိ

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¹ Although not recommended, off-state voltages up to 800V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 6 $A/\mu s$.

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ISOLATION LIMITING VALUE & CHARACTERISTIC

 T_{hs} = 25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _{isol}	R.M.S. isolation voltage from all three terminals to external heatsink	f = 50-60 Hz; sinusoidal waveform; R.H. ≤ 65%; clean and dustfree	-		2500	V
C _{isol}	Capacitance from T2 to external heatsink	f = 1 MHz	-	10	-	pF

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R _{th j-hs}	Thermal resistance junction to heatsink	full or half cycle with heatsink compound without heatsink compound			5.5 7.2	K/W K/W
R _{th j-a}	Thermal resistance junction to ambient	in free air	-	55	-	K/W

STATIC CHARACTERISTICS

T_i = 25 °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MA	X.	UNIT
		BTA204X-			В	C	
I _{GT}	Gate trigger current ²	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$					
		T2+ G+	-	-	50	35	mA
		T2+ G-	-	-	50	35	mA
		T2- G-	-	-	50	35	mA
I _L	Latching current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$					
		T2+ G+	-	-	30	20	mA
		T2+ G-	-	-	45	30	mA
		T2- G-	-	-	30	20	mA
I _H	Holding current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$	-	-	30	20	mA
V_{T}	On-state voltage	$I_{T} = 5 \text{ A}$	-	1.4	1.	.7	V
V _{GT}	Gate trigger voltage	$\dot{V}_{D} = 12 \text{ V}; I_{T} = 0.1 \text{ A}$	-	0.7	1.	.5	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; I_T = 125 °C$	0.25	0.4	-	-	V
I _D	Off-state leakage current	$V_D = V_{DRM(max)}$; $T_j = 125 \text{ °C}$	-	0.1	0.	.5	mA

DYNAMIC CHARACTERISTICS

 $T_j = 25$ °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS		MIN.		UNIT
		BTA204X-	В	C		
dV _D /dt	Critical rate of rise of off-state voltage	V _{DM} = 67% V _{DRM(max)} ; T _j = 125 °C; exponential waveform; gate open circuit	1000	1000	-	V/μs
dl _{com} /dt	Critical rate of change of commutating current	$V_{DM} = 400 \text{ V}; T_j = 125 \text{ °C}; I_{T(RMS)} = 4 \text{ A};$ $dV_{com}/dt = 20V/\mu s; \text{ gate open circuit}$	6	3	-	A/ms
t _{gt}	Gate controlled turn-on time	$I_{TM} = 12 \text{ A}; V_D = V_{DRM(max)}; I_G = 0.1 \text{ A}; $ $dI_G/dt = 5 \text{ A}/\mu\text{s}$	-	-	2	μs

² Device does not trigger in the T2-, G+ quadrant.

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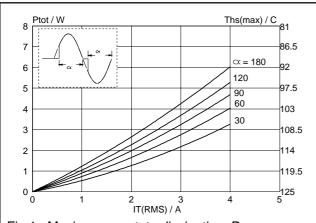


Fig.1. Maximum on-state dissipation, P_{tot} , versus rms on-state current, $I_{T(RMS)}$, where $\alpha = conduction$ angle.

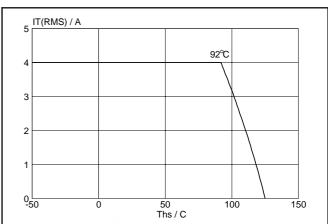


Fig.4. Maximum permissible rms current $I_{\text{T(RMS)}}$, versus heatsink temperature T_{hs} .

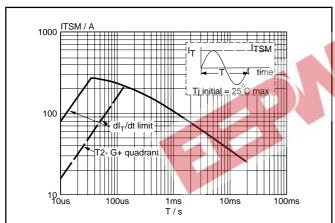


Fig.2. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus pulse width t_p , for sinusoidal currents, $t_p \le 20$ ms.

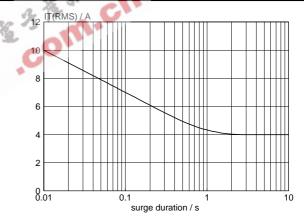


Fig.5. Maximum permissible repetitive rms on-state current $I_{T(RMS)}$, versus surge duration, for sinusoidal currents, f = 50 Hz; $T_{hs} \le 92$ °C.

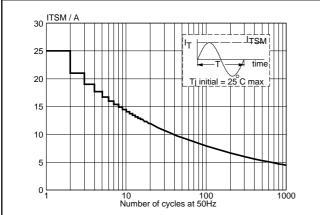


Fig.3. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus number of cycles, for sinusoidal currents, f = 50 Hz.

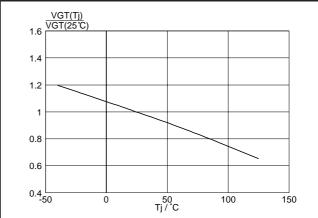
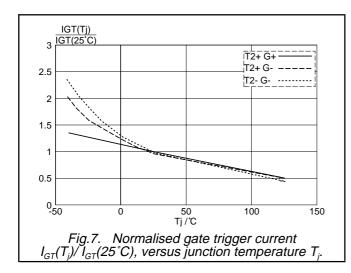
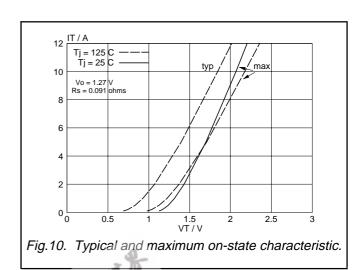
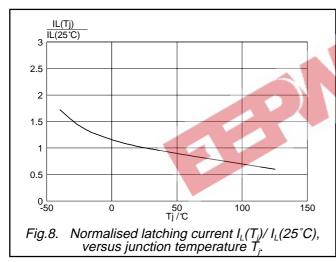


Fig.6. Normalised gate trigger voltage $V_{GT}(T_j)/V_{GT}(25^{\circ}C)$, versus junction temperature T_{j} .

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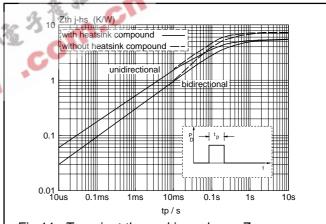


Fig.11. Transient thermal impedance $Z_{th j-hs}$, versus pulse width t_n .

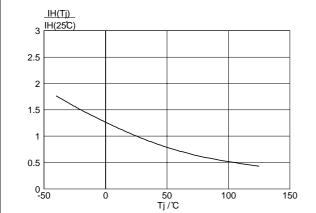
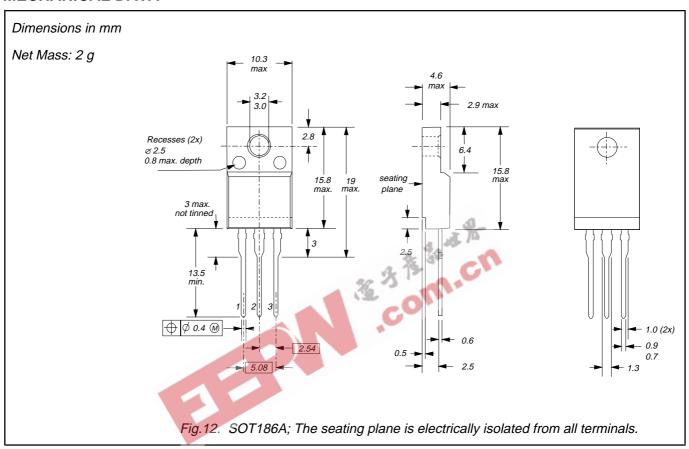


Fig.9. Normalised holding current $I_H(T_i)/I_H(25^{\circ}C)$, versus junction temperature T_i .

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MECHANICAL DATA



- Notes
 1. Refer to mounting instructions for F-pack envelopes.
 2. Epoxy meets UL94 V0 at 1/8".

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DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	

Limiting values

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

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